Seat No.:	Enrolment No.

Subject Code: 180802

Subject Name: VLSI Technologies

GUJARAT TECHNOLOGICAL UNIVERSITY

BE - SEMESTER-VIII • EXAMINATION – WINTER • 2014

Date: 29-11-2014

Time: 02:30 pm - 05:00 pm **Total Marks: 70 Instructions:** 1. Attempt all questions. 2. Make suitable assumptions wherever necessary. 3. Figures to the right indicate full marks. **Q-1** (a) Discuss VLSI design flow in brief. (Y - chart) 7 **(b)** Explain design procedure steps for fabrications of n-MOS transistor. 7 Explain Channel Length Modulation. 7 Q-2 (a) Explain energy band diagram of MOS structure at surface inversion and derive the 7 **(b)** equation of threshold voltage. OR Explain major types of capacitances and show its variation under different 7 **Q-2 (b)** operating regions and physical parameters. Draw the CMOS Inverter circuit and VTC for different operation regions of the 0-37 nMOS and pMOS transistor. Derive critical voltage points Voh, Vol, Vil and Vih. Discuss basic steps of the LOCOS Process. 7 **(b)** OR Q-3 (a) Derive the expression for drain current as a function of VGS, VDS and VSB for all 7 three region of operation of MOSFET using Gradual Channel Approximation. Explain two different down scaling techniques for MOSFET. Which technique is 7 preferable? 7 **Q-4** (a) Explain the functioning of depletion load nMOS inverter and derive critical voltage points Voh, Vol, VIL and VIH. Concept of regularity, modularity and locality. 7 **(b)** Explain delay time definitions for MOS Inverters Switching Characteristics and **Q-4** 7 (a) derive the Expression for λ_{PHL} & λ_{PLH} Writes a short note on Design Quality. **(b)** 7 0-5Discuss Complementary pass transistor logic. Realize the XOR gate using CPL 7 (a) Explain the criteria to measure the design quality to improve the chip design and 7 **(b)** explain any two in brief OR List the important concern for the IC packaging technology. Also Explain different Q-5 (a) 7 packaging technologies. Write a short note on Built In Self Test (BIST). 7 **(b)**
